



Standard 850nm 10 Gbps GaAs PIN Photodiodes

Part number: **PX-CT11**

Features:

- 10 Gbps operation at -3V to 0V
- Two top side wire-bond pads
- Large aperture size
- Extremely low dark current, capacitance, and excellent responsivity

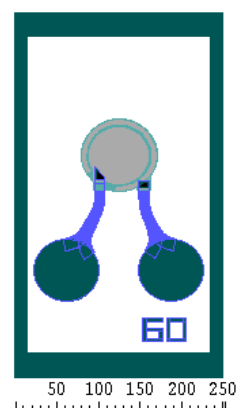
Characteristics (T=300K)

	Conditions	Min.	Typical	Max.	Unit	Notes
Bandwidth	-3V to 0V	8.5			GHz	
Wavelength range	-1.6 V	760	850	860	nm	
Responsivity	-1.6V	0.4	0.55		A/W	@850nm
Dark current	-1.6 V		0.1	1	nA	
Reverse breakdown	1μA	30	50		V	
Capacitance	-3V to 0V		0.25	0.3	pf	
Rise/Fall time				40/40	ps	20%/80%

Physical

	Typical	Unit	Notes
Aperture (dia.)	60	μm	
Bonding pads (dia.)	80	μm	
Die height	150	μm	
Die size	250x460	μm ²	
Substrate	Semi-insulating substrate		

Device performance (at T=300k) and layout [μm]



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